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| Objective |
| Batch name: Process template |
| This process is a guideline on how to spin, develop and rinse CSAR62 on substrates as Si, SiO2 and SOI.CSAR is a semi chemically amplified e-beam resist. The resist has been approved to carry into DTU Danchip cleanroom, but this flow has not been tested or optimized. |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment
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| * 1. Surface treatment
 | BHF dip *or*HMDS | BHF dip for Si substrates (30 sec, H2O 5 min) HMDS treatment for SiO2 and III-V substrates | Generally, pre-treatment is not recommended.  |
| 1. Spin coat of CSAR
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| * 1. Coat wafers
 | Manual Spinner 1, or Spin coater LabSpin | **Resist:** CSAR (AR-P 6200, AllResist)**Spin:** 60 sec @ 4000 rpm (for appr. 180 nm)**Softbake:** 1 min @ 150 oC | Use syringe with filter or disposable pipette (cleaned by N2 gun). Softbake is not a crucial step according to AllResist |
| 1. E-beam exposure
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| * 1. E-beam exposure
 | E-beam writer | Dose: 250 - 350 µC/cm2; a dose-test is required.  | Dose depends strongly on substrate material, thickness of resist, critical dimension and load of pattern. |
| 1. Development & Rinse
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| * 1. Develop-ment
 | Developer (E-beam fumehood) | Develop with AR 600-546, 60 secRinse in IPA, 60 secblow dry with N2 |  |
| 1. De-scum
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| * 1. De-scum
 | BHF dip | BHF dip for Si substrates (30 sec, H2O 5 min).(Never use plasma ash as de-scum, as such a process could generate particles on substrate). | De-scum generally not recommended. If residues appear, optimize dose, development and rinse process. |
| 1. Pattern transfer
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| Please insert which steps you wish to perform after development (e.g. metallization or dry etch). |  |
| 1. Lift-off and Strip
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| * 1. Lift-off
 | Petribowl, E-beamFumehood  | Remover AR 600-71 | USE REMOVER AR 600-71 ONLY AT ROOM TEMPERATURE |